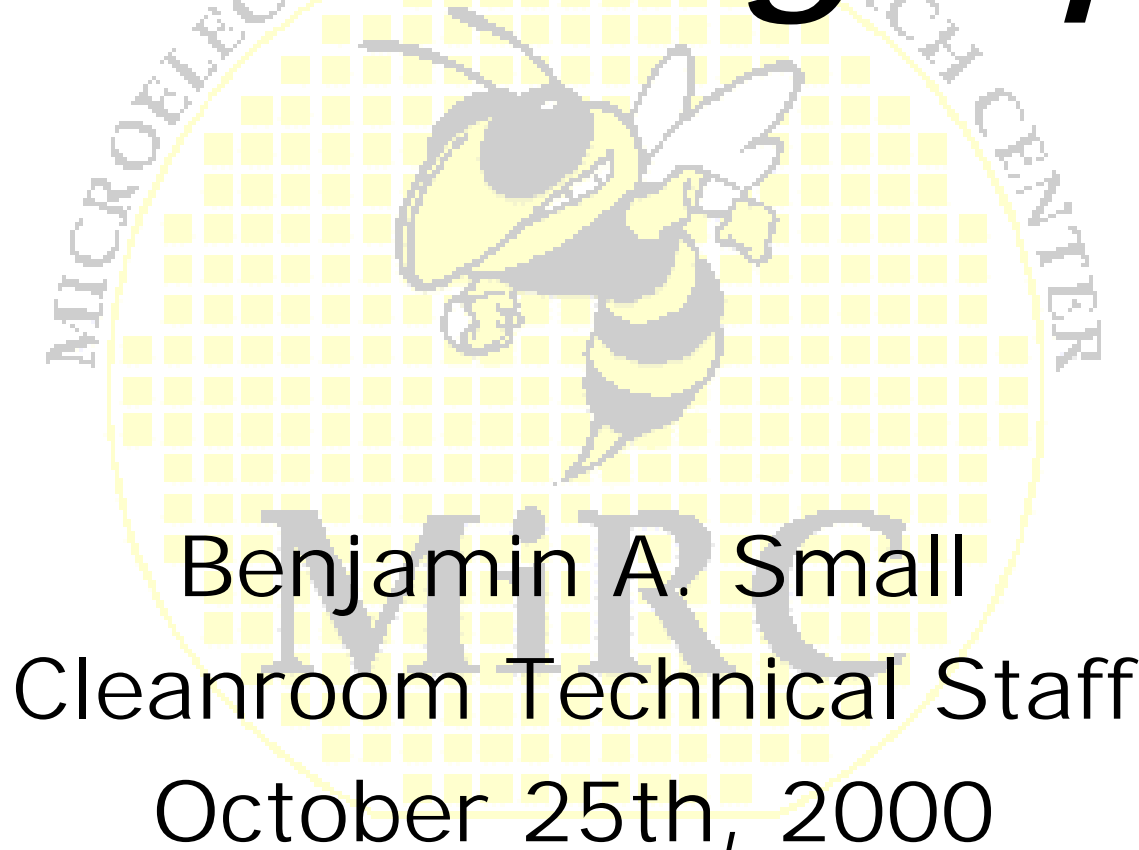


# *Photolithography*



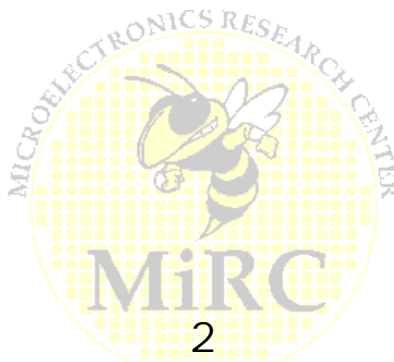
Benjamin A. Small

Cleanroom Technical Staff

October 25th, 2000

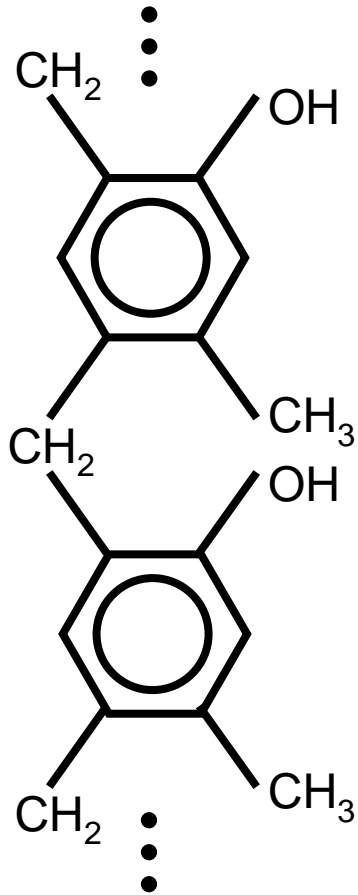
# *Outline*

- Chemistry
- Mechanics
- Procedure
- Spinning
- Exposing
- Comments

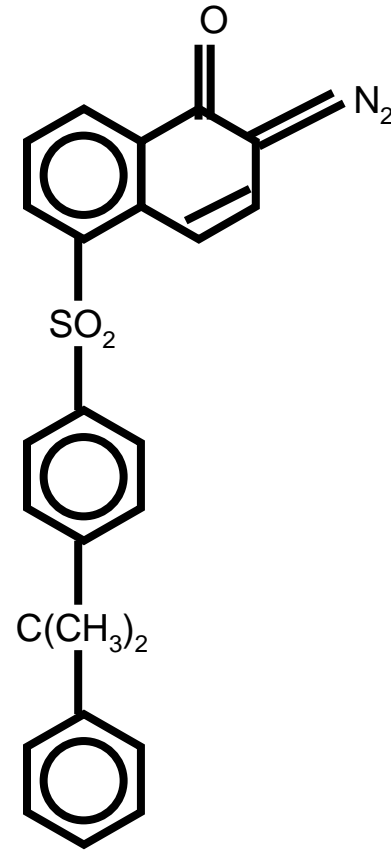


# Chemistry

diazoquinone–novolac (DQN) positive photoresist

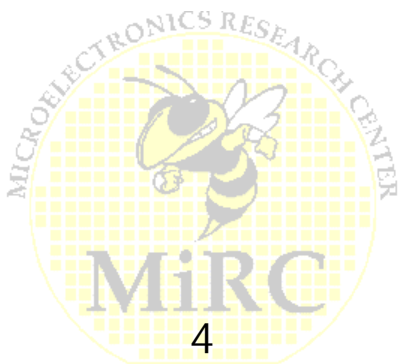
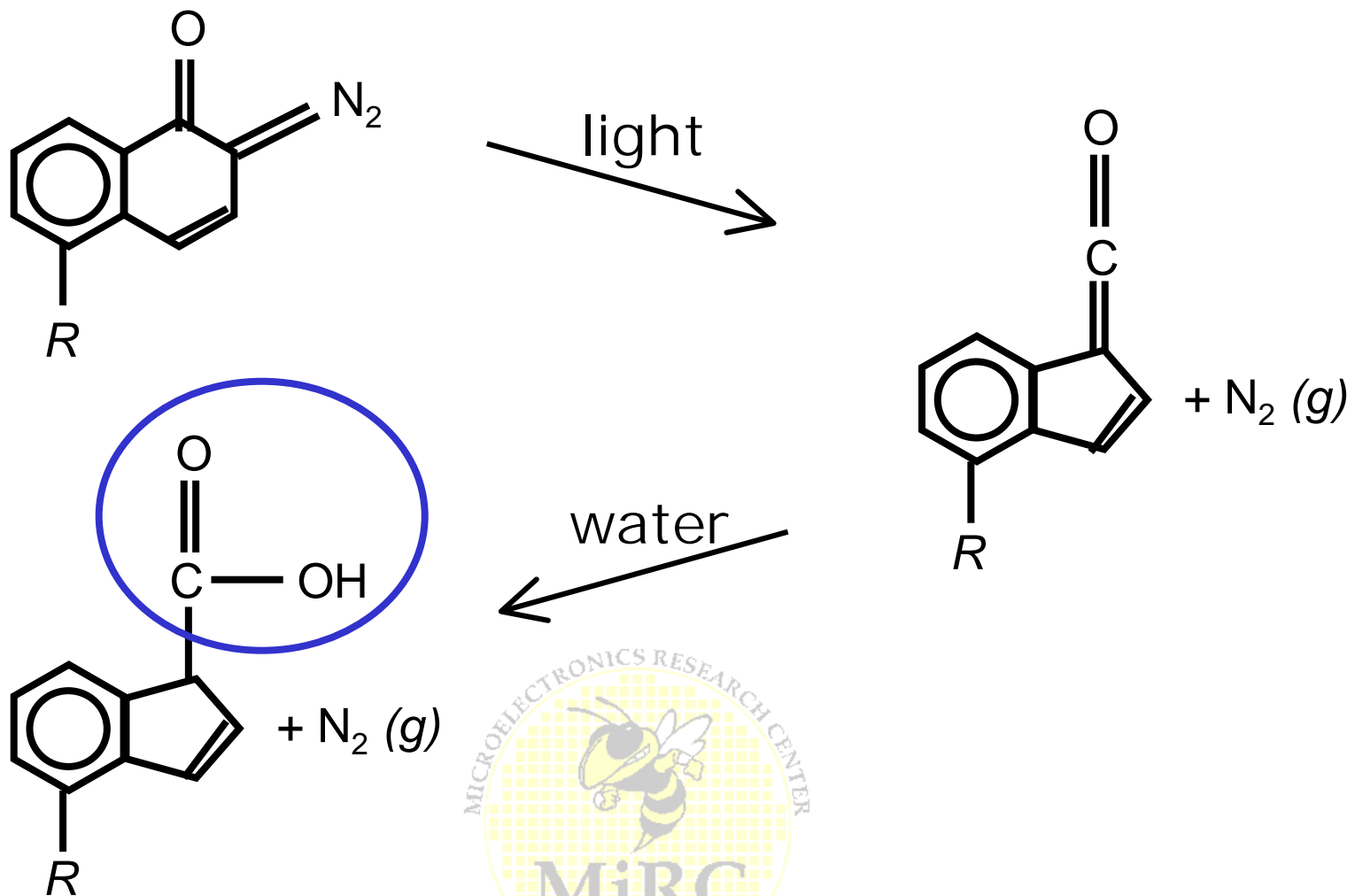


novolac (solvent)

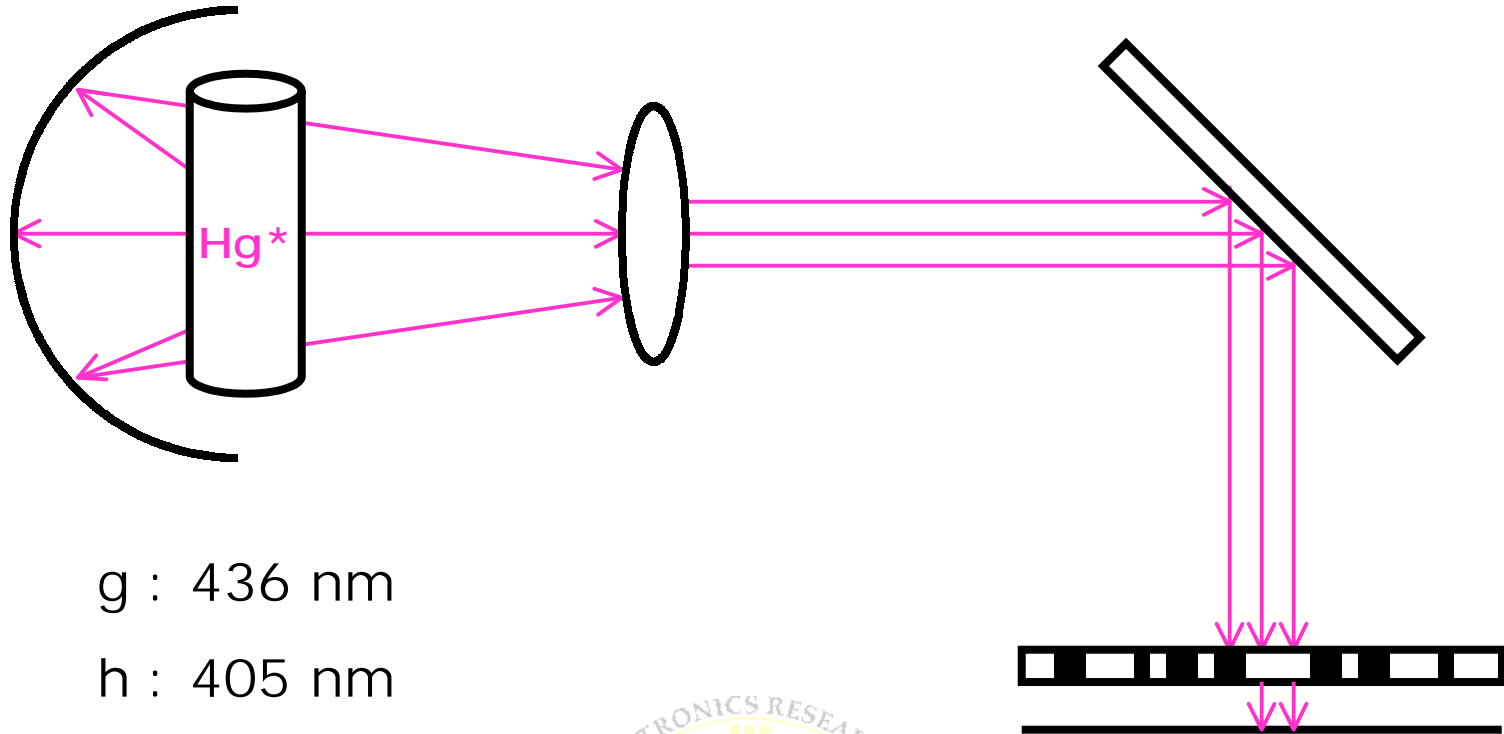


diazoquinone

# Chemistry



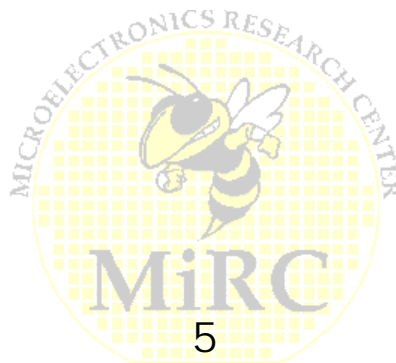
# Mechanics



g : 436 nm

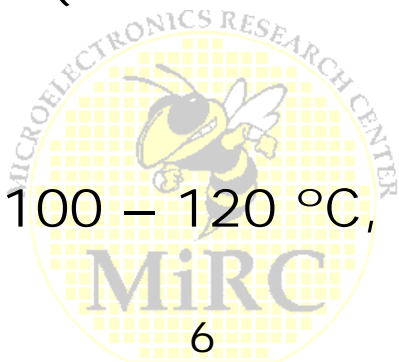
h : 405 nm

i : 365 nm



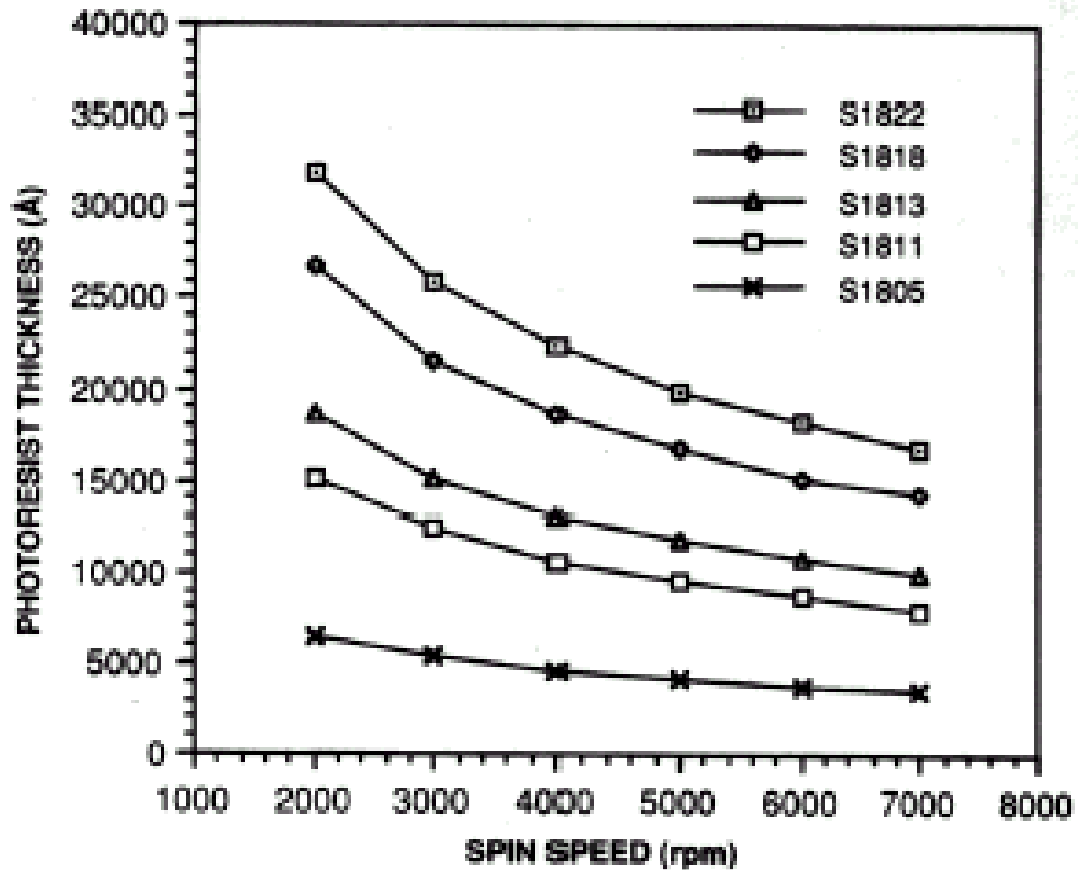
# *Procedure*

- Clean substrate
- Primer (HMDS)
  - Spin
  - Evaporate
- Photoresist
  - Spin
  - Softbake (90 – 115 °C, 1 – 2 min.)
  - Prebake (90 – 110 °C, 0 – 10 min.)
- Exposure
  - Postbake (90 – 115 °C, 0 – 2 min.)
- Develop
  - Rinse
- Hardbake (100 – 120 °C, 10 – 60 min.)



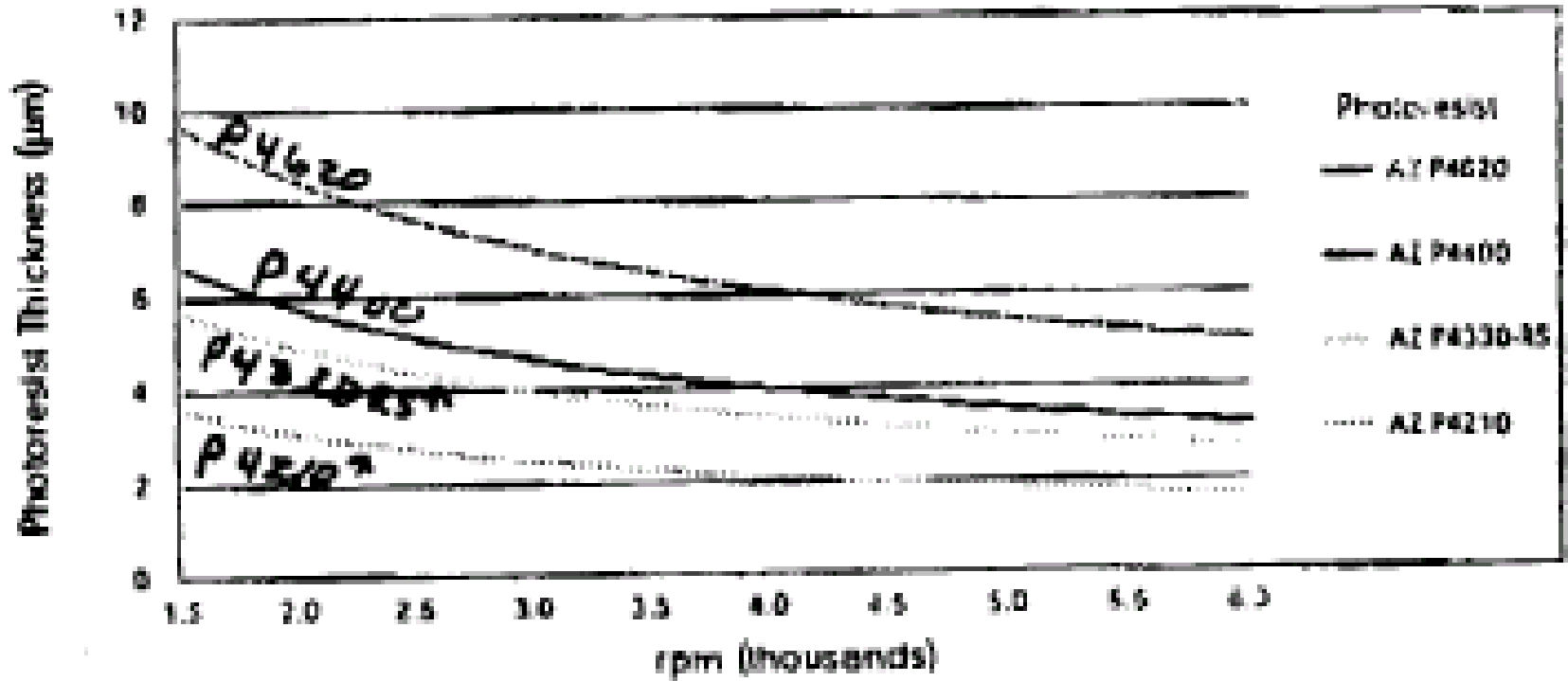
# Spinning

MICROPOSIT S1800 PHOTO RESIST UNDYED SERIES  
Figure 1. Spin Speed Curves



# Spinning

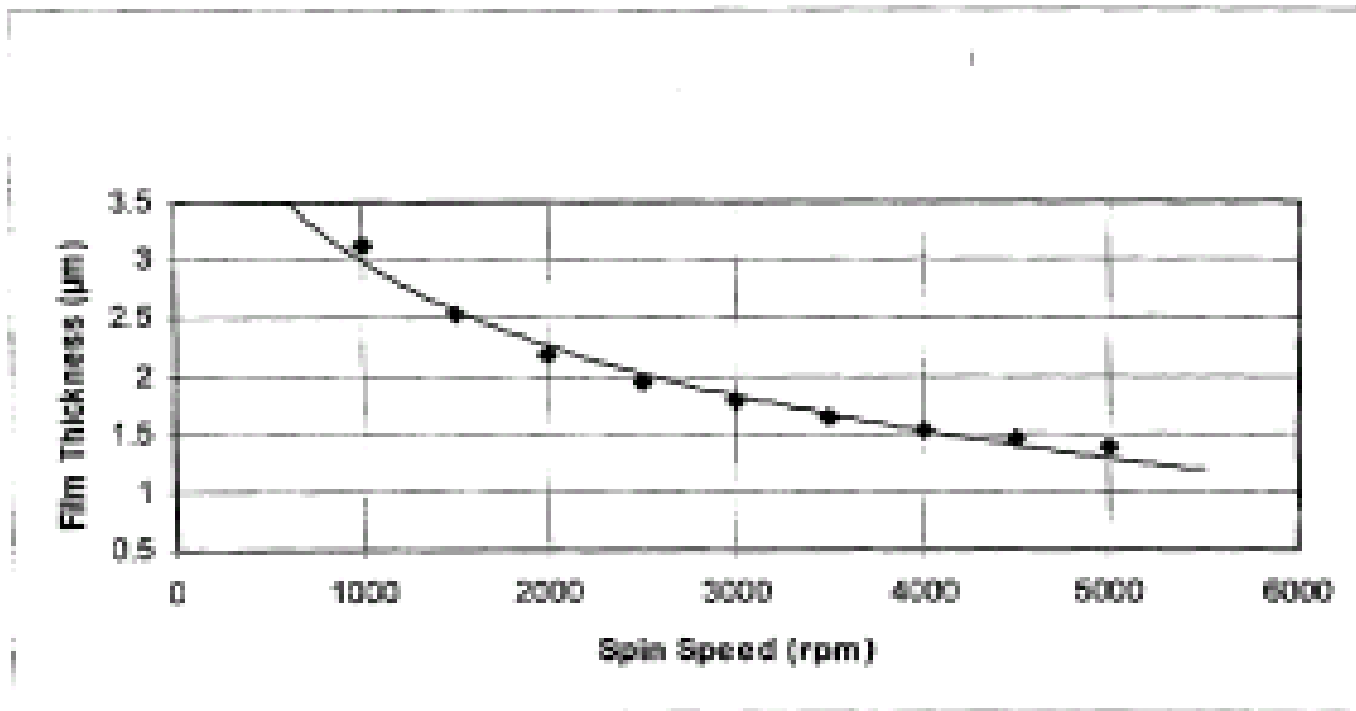
Spin Curve





# *Spinning*

AZ® 5214E - Lot #D99X1  
Spin Speed Curve



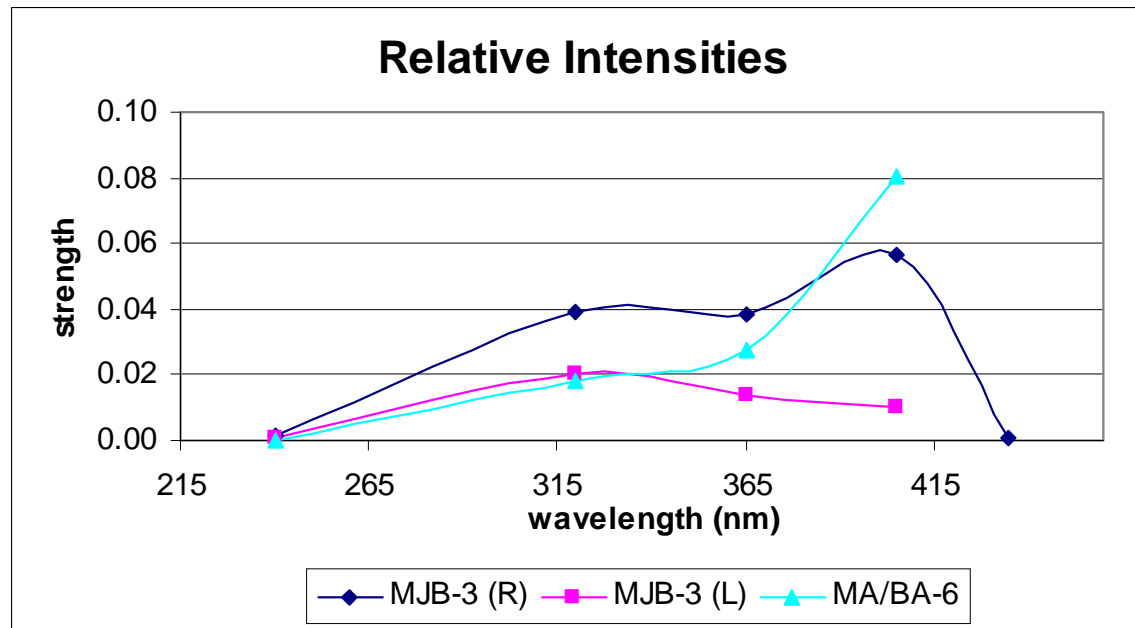
# Exposing

MJB-3 (right): 155 W ("CP"); 195 W ("CI")

MJB-3 (left): 455 W ("CP"); 475 W ("CI")

MA/BA-6: 275 W

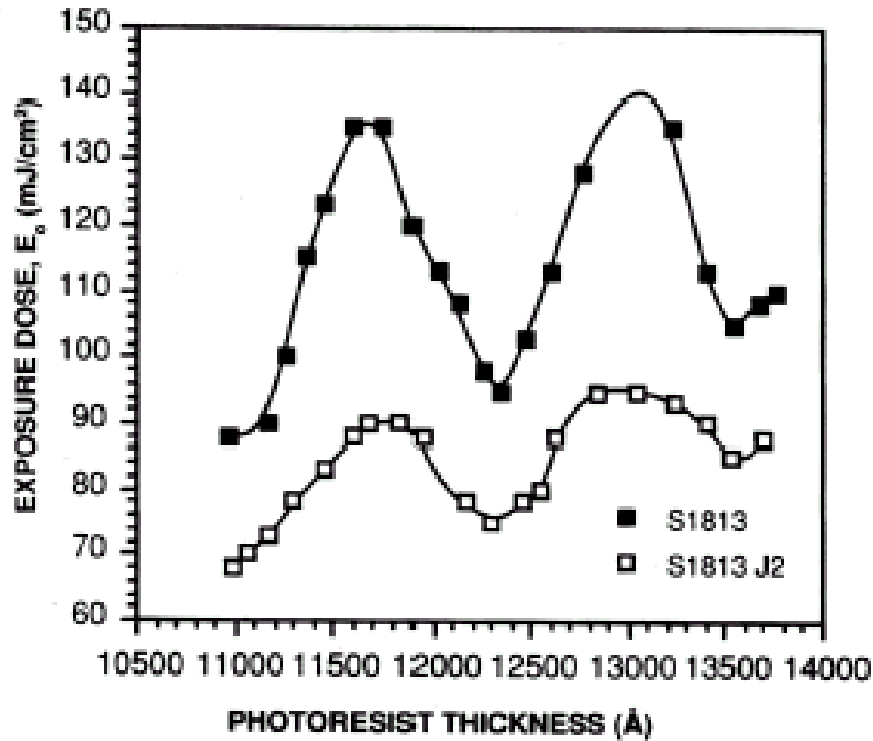
OAI: 7.45 mW/cm<sup>2</sup> @ 365 nm (5 mW/cm<sup>2</sup>)



# Exposing

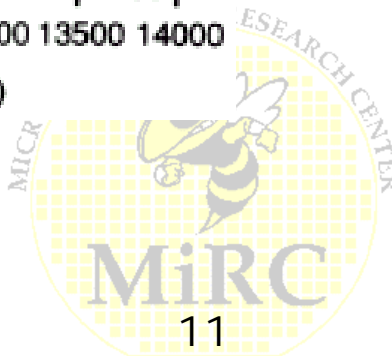
## MICROPOSIT S1813 and S1813 J2 PHOTO RESISTS

Figure 4. Interference Curves

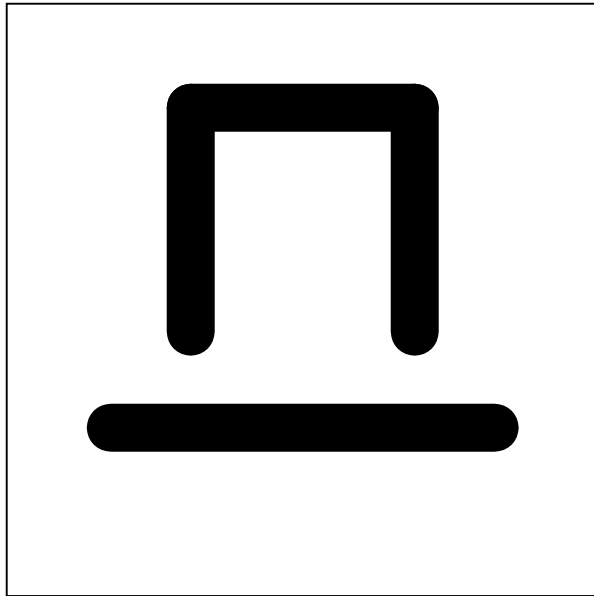


AZ Resists:  
~120 mJ/cm<sup>2</sup> @ 365 nm

(@ 436 nm)

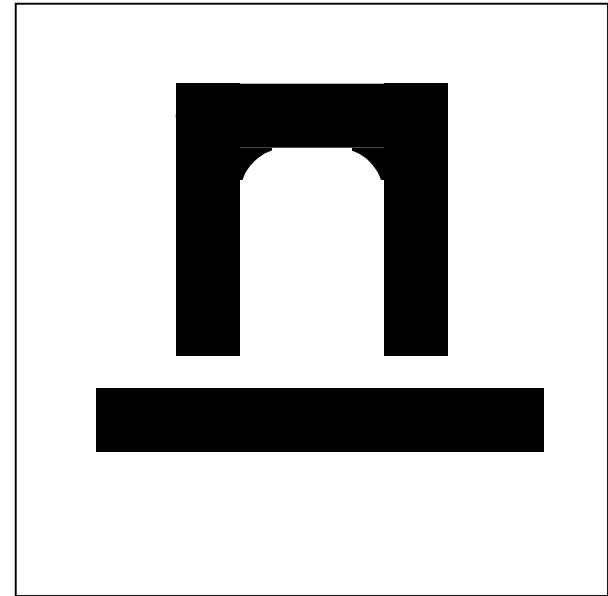


# *Exposing*



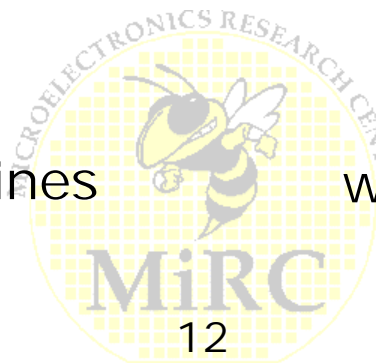
over-exposed,  
over-developed

rounded corners, thin lines



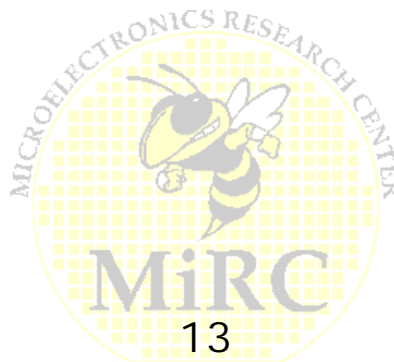
under-exposed,  
under-developed

wide corners, thin spaces



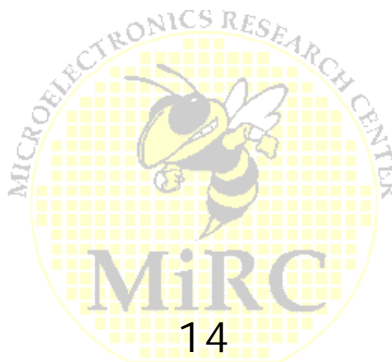
# *Warnings*

- Photoresists are suspected carcinogens and are toxic in large doses
- Prolonged exposure to UV light can cause retinal damage
- Negative developers are also carcinogenic and highly toxic
- Hotplates and ovens are hot



# *Recommendations*

- Photoresist thickness should be less than the critical dimension
- Only spin resists on clean, planar surfaces
- Check lamp intensity often
- Examine features after developing
- Avoid dark-field masks
- Use good alignment marks



# *Bibliography*

Campbell, Stephen A. *The Science and Engineering of Microelectronic Fabrication.* 1996.

Dr. B. Frazier (ECE 6450)

ShIPLEY, Inc.

Clariant Corporation (AZ Electronic Materials)

